Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low $V_F = 0.455$ V at $I_F = 5$ A

Features

- Fine Lithography Trench–based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- Pb-Free and Halide-Free Packages are Available

Typical Applications

- Switching Power Supplies including Notebook / Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC–DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics

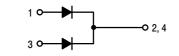
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

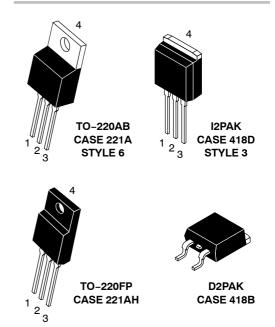


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PIN CONNECTIONS





ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

1

MAXIMUM RATINGS

| Rating | | Symbol | Value | Unit |
|--|-------------------------|--|-------------|------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | | V _{RRM} V _{RWM} V _R | 100 | V |
| Average Rectified Forward Current (Rated V_R , T_C = 115°C) | Per device Per diode | I _{F(AV)} | 30 15 | A |
| Peak Repetitive Forward Current (Rated V _R , Square Wave, 20 kHz, T _C = 110°C) | Per device Per diode | I _{FRM} | 60 30 | A |
| Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz) | | I _{FSM} | 160 | A |
| Operating Junction Temperature | | TJ | -40 to +150 | °C |
| Storage Temperature | | T _{stg} | -40 to +150 | °C |
| Voltage Rate of Change (Rated V _R) | | dv/dt | 10,000 | V/μs |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

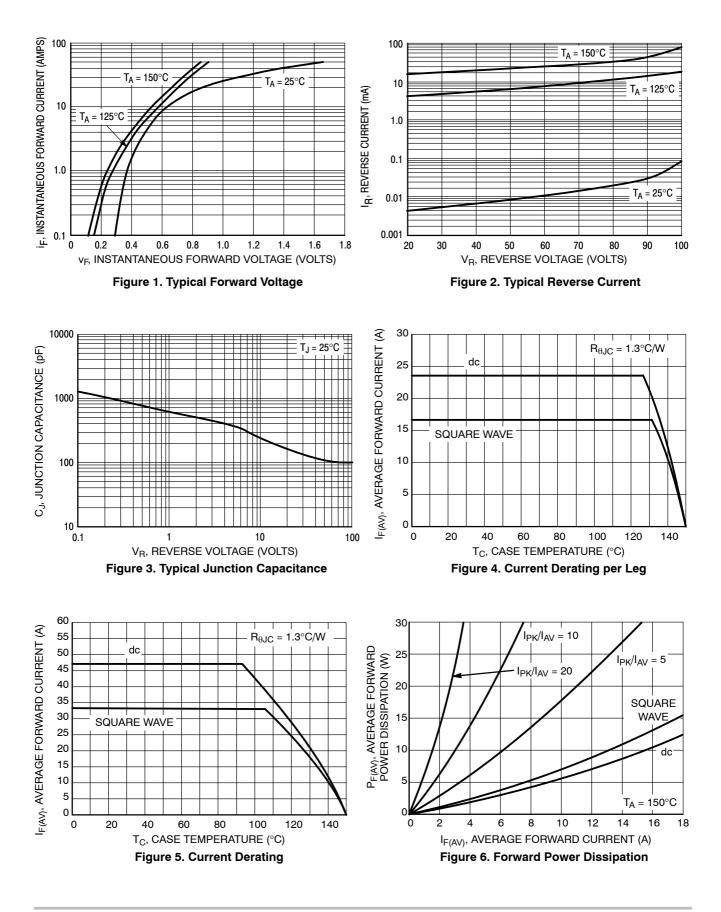
THERMAL CHARACTERISTICS

| Rating | Symbol | NTST30100CTG, NTSB30100CT-1G | NTSB30100CTG | NTSJ30100CTG | Unit |
|---|--------|---------------------------------|--------------|--------------|--------------|
| Maximum Thermal Resistance per Diode Junction-to-Case Junction-to-Ambient | 000 | 2.5 70 | 1.14 46.6 | 4.09 105 | °C/W °C/W |

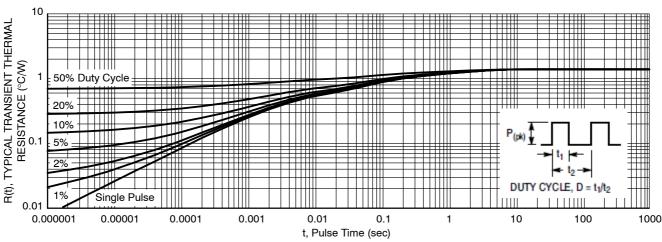
ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

| Rating | Symbol | Тур | Мах | Unit |
|---|----------------|-------------------------|----------------|----------|
| | ۷F | 0.516 0.576 0.734 | - - 0.85 | V |
| $(I_F = 5 A, T_J = 125^{\circ}C)$ $(I_F = 7.5 A, T_J = 125^{\circ}C)$ $(I_F = 15 A, T_J = 125^{\circ}C)$ | | 0.455 0.522 0.627 | _ _ 0.68 | |
| Maximum Instantaneous Reverse Current (Note 1) $(V_R = 70 \text{ V}, T_J = 25^{\circ}\text{C})$ $(V_R = 70 \text{ V}, T_J = 125^{\circ}\text{C})$ | I _R | 7.2 8.0 | | μA mA |
| (Rated dc Voltage, $T_J = 25^{\circ}C$) (Rated dc Voltage, $T_J = 125^{\circ}C$) | | 65 20 | 500 35 | μA mA |

1. Pulse Test: Pulse Width = 300 $\mu s,$ Duty Cycle $\,\leq\,$ 2.0%



TYPICAL CHARACTERISITICS



TYPICAL CHARACTERISITICS

Figure 7. Typical Transient Thermal Response, Junction-to-Case for NTST30100CT and NTSB30100CT-1G

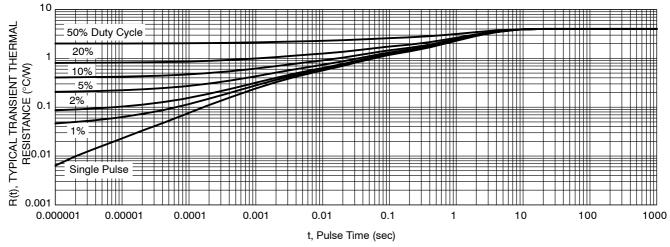
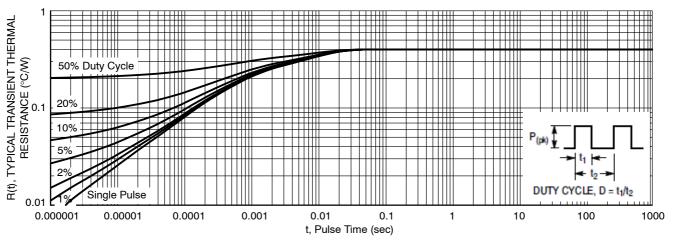


Figure 8. Typical Transient Thermal Response, Junction-to-Case for NTSJ30100CTG





ORDERING INFORMATION

| Device | Package | Shipping |
|----------------|---------------------------------|-------------------|
| NTST30100CTG | TO-220AB (Pb-Free) | 50 Units / Rail |
| NTSB30100CT-1G | l ² PAK (Pb–Free) | 50 Units / Rail |
| NTSJ30100CTG | TO-220FP (Halide-Free) | 50 Units / Rail |
| NTSB30100CTG | D ² PAK (Pb–Free) | 50 Units / Rail |
| NTSB30100CTT4G | D ² PAK (Pb–Free) | 800 / Tape & Reel |

AY WW AY WW TS30100CG AY WW AKA TS30100CG TS30100Cx TS30100CG AKA AKA AKA AYWW TO-220FP I²PAK D²PAK TO-220AB ocation

MARKING DIAGRAMS

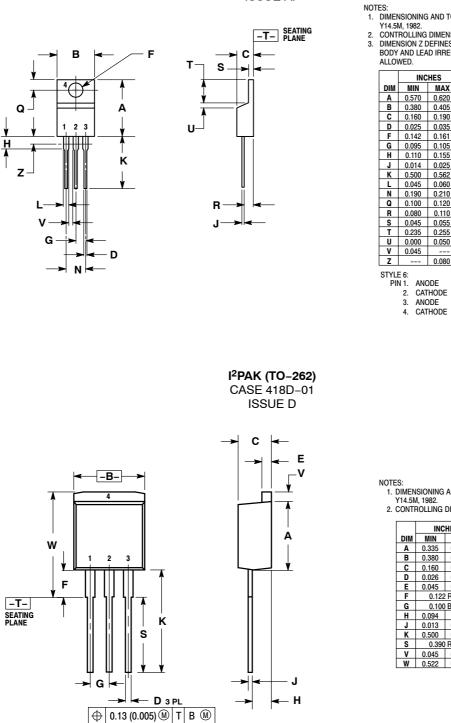
| А | = Assembly Lo |
|---|---------------|
| V | - Voar |

| r | = rear |
|-------|----------|
| ۸/۱۸/ | – Work W |

- = Work Week WW AKA = Polarity Designator
- х = G or H
- G = Pb-Free Package
- Н = Halide-Free Package

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AF**



ILES: DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| | INCHES MILLIMET | | IETERS | |
|-----|-----------------|-------|--------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.570 | 0.620 | 14.48 | 15.75 |
| В | 0.380 | 0.405 | 9.66 | 10.28 |
| С | 0.160 | 0.190 | 4.07 | 4.82 |
| D | 0.025 | 0.035 | 0.64 | 0.88 |
| F | 0.142 | 0.161 | 3.61 | 4.09 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| Н | 0.110 | 0.155 | 2.80 | 3.93 |
| J | 0.014 | 0.025 | 0.36 | 0.64 |
| ĸ | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| Ν | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| Т | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| ۷ | 0.045 | | 1.15 | |
| Ζ | | 0.080 | | 2.04 |

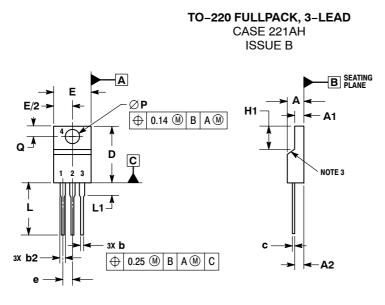
2. 3. ANODE

CATHODE 4.

NOTES: DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: INCH.

| | INCHES | | MILLIN | IETERS | |
|-----|---------------|-------|--------|--------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 0.335 | 0.380 | 8.51 | 9.65 | |
| В | 0.380 | 0.406 | 9.65 | 10.31 | |
| С | 0.160 | 0.185 | 4.06 | 4.70 | |
| D | 0.026 | 0.035 | 0.66 | 0.89 | |
| Е | 0.045 | 0.055 | 1.14 | 1.40 | |
| F | 0.122 REF 3.1 | | 3.10 | 0 REF | |
| G | 0.100 | BSC | 2.54 | BSC | |
| Н | 0.094 | 0.110 | 2.39 | 2.79 | |
| J | 0.013 | 0.025 | 0.33 | 0.64 | |
| K | 0.500 | 0.562 | 12.70 | 14.27 | |
| S | 0.390 REF | | 9.90 | REF | |
| ٧ | 0.045 | 0.070 | 1.14 | 1.78 | |
| W | 0.522 | 0.551 | 13.25 | 14.00 | |

PACKAGE DIMENSIONS



NOTES:

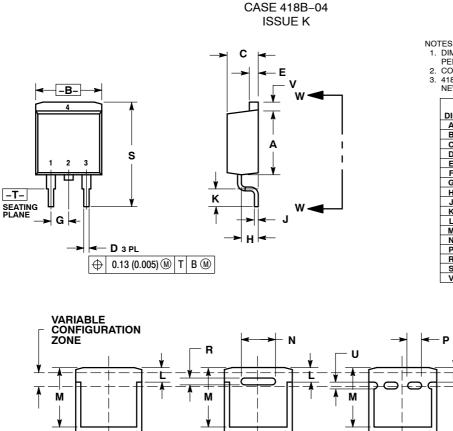
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. CONTOUL UNCONTROLLED IN THIS AREA. 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY. 5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.00.

| | SHALL NOT EXCEED 2.0 | | | |
|-----|----------------------|-------|--|--|
| | MILLIMETERS | | | |
| DIM | MIN | MAX | | |
| Α | 4.30 | 4.70 | | |
| A1 | 2.50 | 2.90 | | |
| A2 | 2.50 | 2.70 | | |
| b | 0.54 | 0.84 | | |
| b2 | 1.10 | 1.40 | | |
| C | 0.49 | 0.79 | | |
| D | 14.70 | 15.30 | | |
| Е | 9.70 | 10.30 | | |
| е | 2.54 | BSC | | |
| H1 | 6.70 | 7.10 | | |
| L | 12.70 | 14.73 | | |
| L1 | | 2.80 | | |
| Ρ | 3.00 | 3.40 | | |
| Q | 2.80 | 3.20 | | |

PACKAGE DIMENSIONS

D²PAK 3

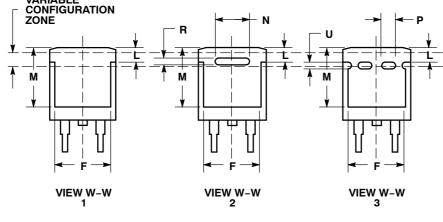


1. DIMENSIONING AND TOLERANCING PER ANSI V14 5M 1982

PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. 418B-01 THRU 418B-03 OBSOLETE

418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

| | INCHES | | MILLIMETER | |
|-----|-----------|-------|------------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 0.340 | 0.380 | 8.64 | 9.65 |
| в | 0.380 | 0.405 | 9.65 | 10.29 |
| С | 0.160 | 0.190 | 4.06 | 4.83 |
| D | 0.020 | 0.035 | 0.51 | 0.89 |
| Е | 0.045 | 0.055 | 1.14 | 1.40 |
| F | 0.310 | 0.350 | 7.87 | 8.89 |
| G | 0.100 BSC | | 2.54 | BSC |
| Н | 0.080 | 0.110 | 2.03 | 2.79 |
| J | 0.018 | 0.025 | 0.46 | 0.64 |
| ĸ | 0.090 | 0.110 | 2.29 | 2.79 |
| L | 0.052 | 0.072 | 1.32 | 1.83 |
| м | 0.280 | 0.320 | 7.11 | 8.13 |
| N | 0.197 REF | | 5.00 REF | |
| Р | 0.079 REF | | 2.00 REF | |
| R | 0.039 | REF | 0.99 | REF |
| S | 0.575 | 0.625 | 14.60 | 15.88 |
| V | 0.045 | 0.055 | 1.14 | 1.40 |



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